

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT3S05T

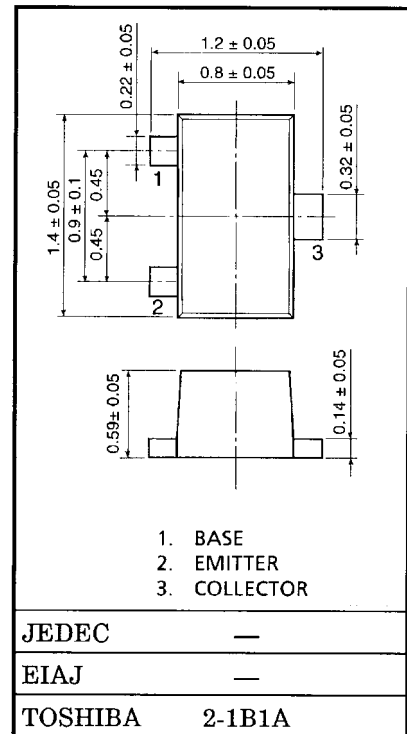
VHF~UHF Band Low Noise Amplifier Applications

- Suitable for use in an OSC
- Low noise figure
NF = 1.4dB
- Excellent collector current linearity
 $|S_{21e}|^2 = 8.5\text{dB}$ (@1 V/5 mA/1 GHz)

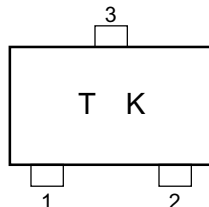
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	10	V
Collector-emitter voltage	V _{CEO}	5	V
Emitter-base voltage	V _{EBO}	2	V
Collector current	I _C	40	mA
Base current	I _B	10	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _J	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Unit in mm



Marking



000707EAA1

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Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	2	4.5	—	GHz
Insertion gain	$ S_{21e} ^2(1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	8.5	—	dB
	$ S_{21e} ^2(2)$	$V_{CE} = 3\text{ V}, I_C = 20\text{ mA}, f = 1\text{ GHz}$	8.5	11.5	—	
Noise figure	NF	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	1.4	2.2	dB

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	80	—	140	—
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note)	—	0.9	1.25	pF

Note: C_{re} is measured by 3 terminal method with capacitance bridge.

Caution

This device electrostatic sensitivity. Please handle with caution.